

## Amendments to the Specification

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### **Abstract**

~~Patterning method, and field effect transistors~~

~~An explanation is given of, inter alia, a~~ A patterning method, ~~in which with~~ a filling material (22) with a T-shaped cross section is used as a mask during patterning ~~in~~ order to produce structures having sublithographic dimensions, ~~in particular such as~~ a double-fin field effect transistor.

(Figure 1B)